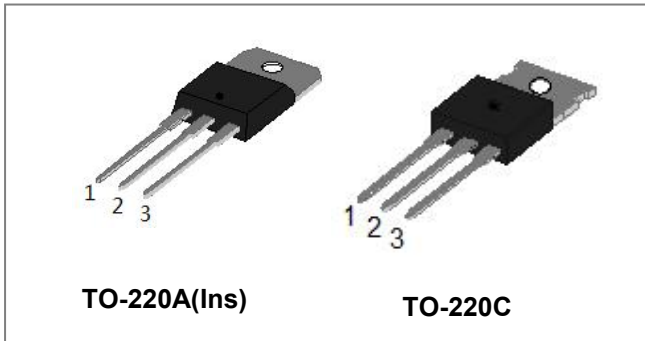
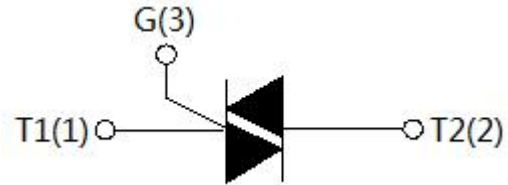


SST12 Series 12A TRIACs



Circuit Diagram



Description

With high ability to withstand the shock loading of large current, SST12 series triacs provide high dv/dt rate with strong resistance to electromagnetic interference. With high commutation performances, 3 quadrant products especially recommended for use on inductive load.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Storage junction temperature range	T_{stg}	-	-40-150	°C
Operating junction temperature range	T_j	-	-40-125	°C
Repetitive peak off-state voltage($T_j=25^\circ\text{C}$)	V_{DRM}	-	600/800	V
Repetitive peak reverse voltage($T_j=25^\circ\text{C}$)	V_{RRM}	-	600/800	V
Non repetitive surge peak Off-state voltage	V_{DSM}	-	$V_{DRM} + 100$	V
Non repetitive peak reverse voltage	V_{RSM}	-	$V_{RRM} + 100$	V
RMS on-state current	$I_{(TRMS)}$	TO-220A(Ins)($T_c=90^\circ\text{C}$)	12	A
		TO-220C($T_c=105^\circ\text{C}$)		
Non repetitive surge peak on-state current (full cycle, F=50Hz)	I_{TSM}	-	120	A
I^2t value for fusing ($t_p=10\text{ms}$)	I^2t	-	78	A ² s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$)	di/dt	-	50	A/ μs
Peak gate current	I_{GM}	-	4	A
Average gate power dissipation	$P_{G(AV)}$	-	1	W
Peak gate power	P_{GM}	-	5	W

Electrical Characteristics($T_j=25^\circ\text{C}$ unless otherwise specified)

3 Quadrants

Symbol	Test Condition	Quadrant		Value		Unit
				BW	CW	
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	I - II - III	MAX	50	35	mA
V_{GT}		I - II - III	MAX	1.3		V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ\text{C} R_L=3.3\text{K}\Omega$	I - II - III	MIN	0.2		V
I_L	$I_G=1.2I_{GT}$	I - III	MAX	80	50	mA
		II		90	60	
I_H	$I_T=100\text{mA}$		MAX	60	40	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$		MIN	1000	500	V/ μs

4 Quadrants

Symbol	Test Condition	Quadrant		Value		Unit
				B	C	
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	I - II - III	MAX	50	25	mA
		IV		70	50	
V_{GT}	ALL		MAX	1.3		V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ\text{C} R_L=3.3\text{K}\Omega$	ALL	MIN	0.2		V
I_L	$I_G=1.2I_{GT}$	I - III - IV	MAX	50	40	mA
		II		100	80	
I_H	$I_T=100\text{mA}$		MAX	50	25	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$		MIN	500	200	V/ μs

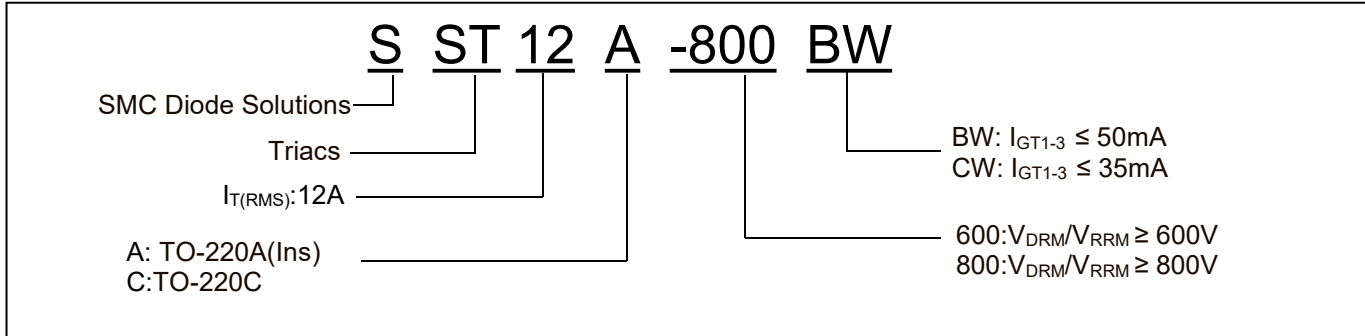
Static Characteristics

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=17\text{A } t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.5	V
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	μA
I_{RRM}		$T_j=125^\circ\text{C}$	1	mA

Thermal Resistances

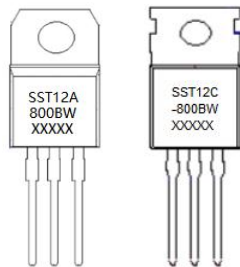
Symbol	Condition		Value	Units
$R_{th(j-c)}$	Junction to case(AC)	TO-220A(Ins)	2.3	$^\circ\text{C/W}$
		TO-220C	1.4	$^\circ\text{C/W}$

Ordering Information



Device	Package	Shipping
SST12A-800CW, SST12A-800BW, SST12A-600BW	TO-220A(Ins)	50pcs/ Tube
SST12C-800CW, SST12C-800BW	TO-220C	50pcs/ Tube

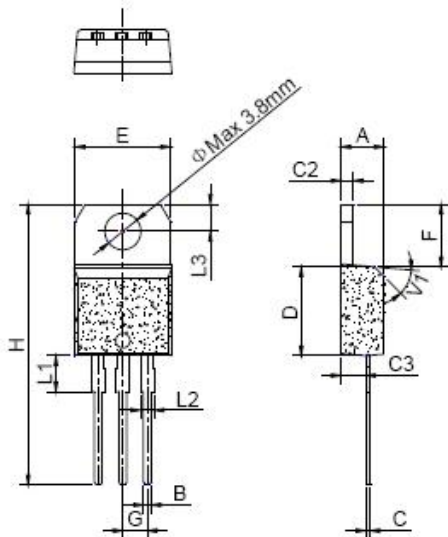
Marking Diagram



Where XXXXX is YYWWL

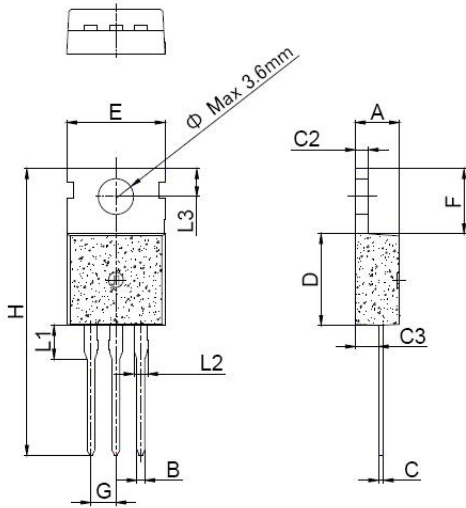
SST12A-800BW = Part name
SST12C-800BW = Part name
YY = Year
WW = Week
L = Lot Number

Mechanical Dimensions TO-220A(Ins)



SYMBOL	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.60		10.4	0.378		0.409
F	6.55		6.95	0.258		0.274
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

Mechanical Dimensions TO-220C



SYMBOL	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.23		1.32	0.048		0.052
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.39		0.406
F	6.30		6.90	0.248		0.272
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.39			0.133	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
φ		3.6			0.142	

Ratings and Characteristics Curves

FIG.1 Maximum power dissipation versus RMS on-state current

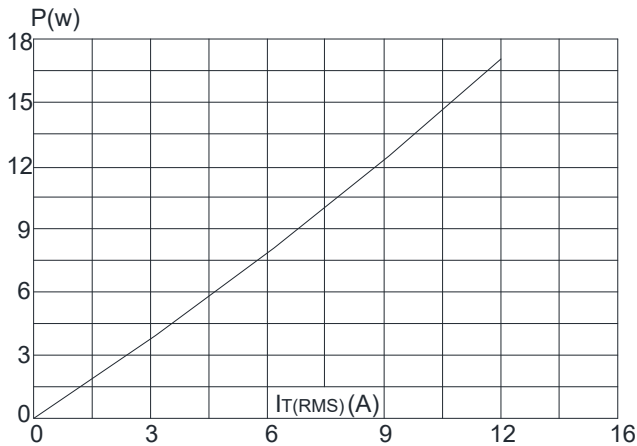


FIG.2: RMS on-state current versus case temperature

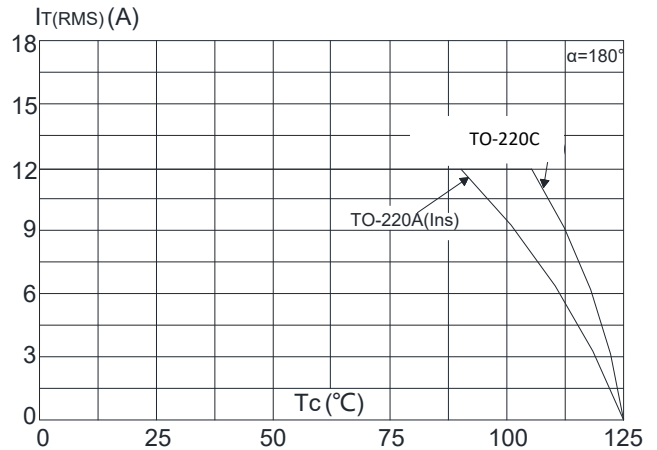


FIG.3: Surge peak on-state current versus number of cycles

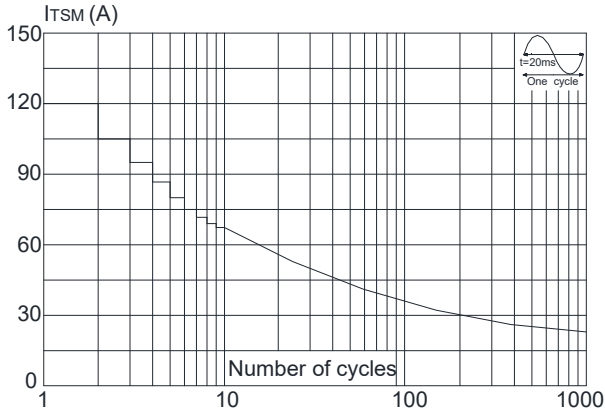


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($dI/dt(I-I-II-III) < 50\text{A}/\mu\text{s}$)

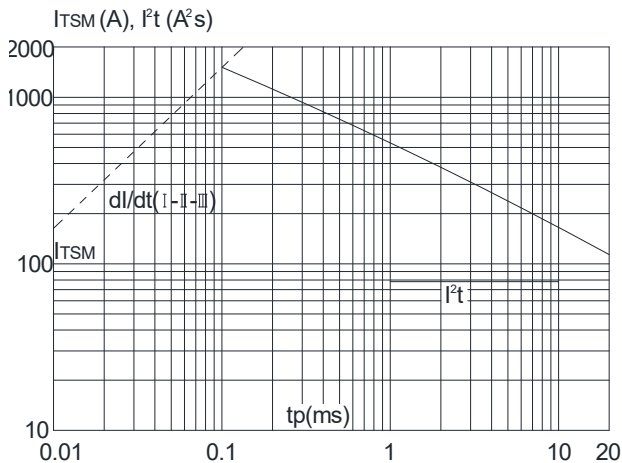


FIG.4: On-state characteristics (maximum values)

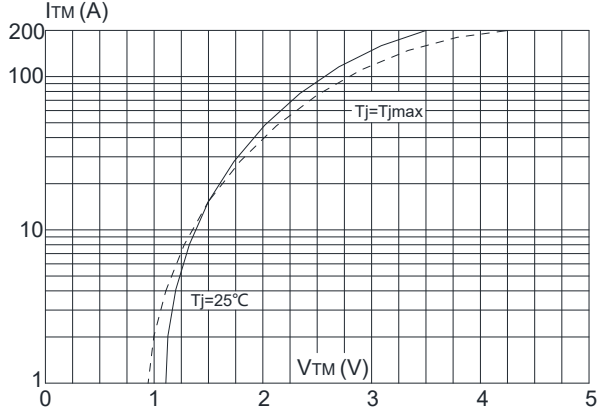
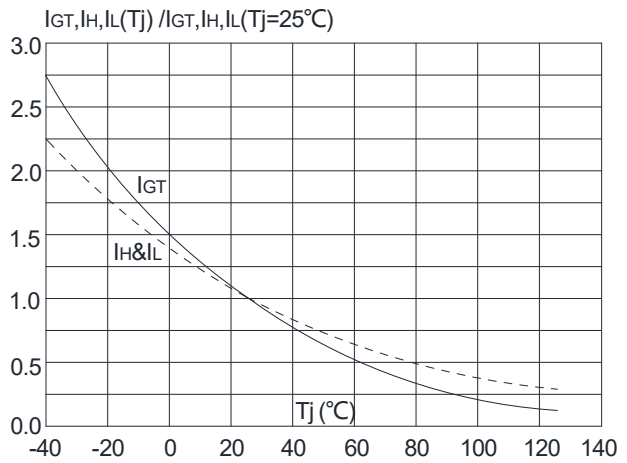


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



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